

changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

1. (amended) A method of forming a fluorine doped insulating material comprising:
- providing a substrate within a reaction chamber, the reaction chamber controlled within a range of temperatures from above 400 degrees Celsius ($^{\circ}\text{C}$) but not greater than about 700°C ;
- providing reactants comprising silicon, fluorine and ozone within the reaction chamber and maintaining a pressure within the reaction chamber of from about 400 Torr to about 1 atmosphere; and
- depositing an insulating material, at a rate of from about 1000 angstroms per minute ($\text{\AA}/\text{min}$) to about 10000 $\text{\AA}/\text{min}$, comprising fluorine, silicon and oxygen onto the substrate from the reactants, wherein the depositing occurs with a plasma being present in the reaction chamber.
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10. (amended) The method of claim 1 comprising maintaining a pressure within the reaction chamber at about 600 Torr during the depositing.
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18. (twice amended) A method of forming a silicon oxide having Si-F bonds, comprising:

providing a reaction chamber at a temperature in excess of 400 degrees Celsius (°C) but less than 630°C;

positioning a substrate within the reaction chamber;

providing an ozone comprising reactant and a precursor having Si-F bonds to the substrate within the reaction chamber and maintaining a pressure within the reaction chamber of from about 400 Torr to about 1 atmosphere;

while providing the ozone comprising reactant and the precursor having Si-F bonds to the substrate, providing a plasma within the reaction chamber; and

causing a silicon oxide having Si-F bonds, to deposit onto the substrate within the reaction chamber at a rate of from about 1000 angstroms per minute (Å/min) to about 10000 Å/min.

38. (amended) The method of claim 18 comprising maintaining a temperature within the reaction chamber in excess of 500°C but less than 630°C during the depositing.

43. (amended) The method of claim 18 comprising maintaining a temperature within the reaction chamber from about 500°C to about but less than 630°C during the depositing.

45. (new) A method of forming an insulating material comprising:
- providing a substrate within a reaction chamber;
 - providing reactants comprising silicon, fluorine and ozone within the reaction chamber and maintaining a pressure within the reaction chamber of from about 400 Torr to about 1 atmosphere; and
 - with a plasma present in the reaction chamber, depositing an insulating material comprising fluorine, silicon and oxygen onto the substrate from the reactants.
46. (new) A method of forming a silicon oxide having Si-F bonds, comprising:
- providing a substrate within a reaction chamber;
 - providing reactants comprising ozone and a precursor having Si-F bonds and maintaining a pressure of from about 400 Torr to about 1 atmosphere; and
 - with a plasma present in the reaction chamber, depositing a silicon oxide having Si-F bonds onto the substrate from the reactants.
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